

# SIMPA & METIS models


## Proton cross section from heavy ion data

COMET-ENV  
"Tools to predict Single Event Effects"

# SIMPA & METIS

- Prediction tools from heavy ions to protons
- No technological input parameters: end-user tool
- Fast calculations
- ECSS-Q-ST-60-15C: *For SEUs, proton cross-section curve can be obtained from heavy ion cross-section curve with simulation tools such as SIMPA or PROFIT;  
The following RDM shall be applied on calculated error rate: 10, when proton error rate is based on simulation from heavy ion data;*

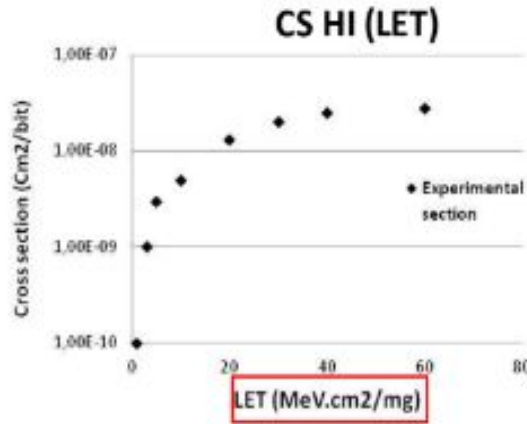
# SIMPA overview

- **SIM**ulation of **P**roton **A**ccelerator
- Semi-empirical model developed by Matra Marconi Space in 1995
- Implemented in the OMERE tool suite 
- SEU predictions for devices (DRAMs,  $\mu$ processors, SRAMs) with sensitive thicknesses  $> 2 \mu\text{m}$  (no SOI)
- Integration of the heavy-ion cross-section with the probability  $\Phi_{Ep}$  to deposit given energy ( $E_d$ ) from the secondary recoils of p-Si

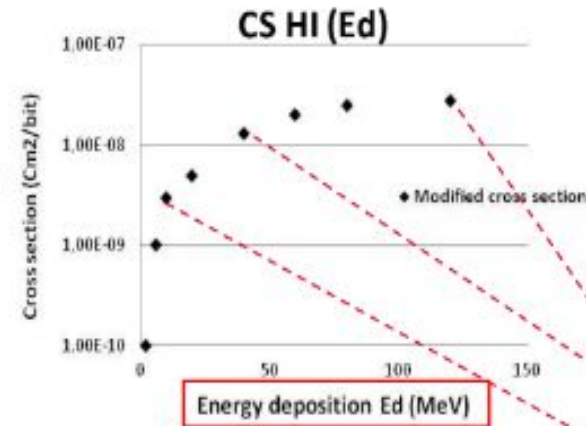
$$\sigma(E_p) = \int_0^{E_p} \sigma_{IL}(E_d) \cdot \Phi_{Ep}(E_d) \cdot dE_d$$

- Experimental data of the energy deposition in diodes and comparison with HETC nuclear code
  - The probability  $\Phi_{Ep}$  of the deposited energy/ $\mu\text{m}$  is a function of the deposited energy and four parameters that depend on the incident proton energy and the thickness
  - For the implementation in OMERE, the variation with thickness is neglected and a sensitive thickness of  $6 \mu\text{m}$  is considered.

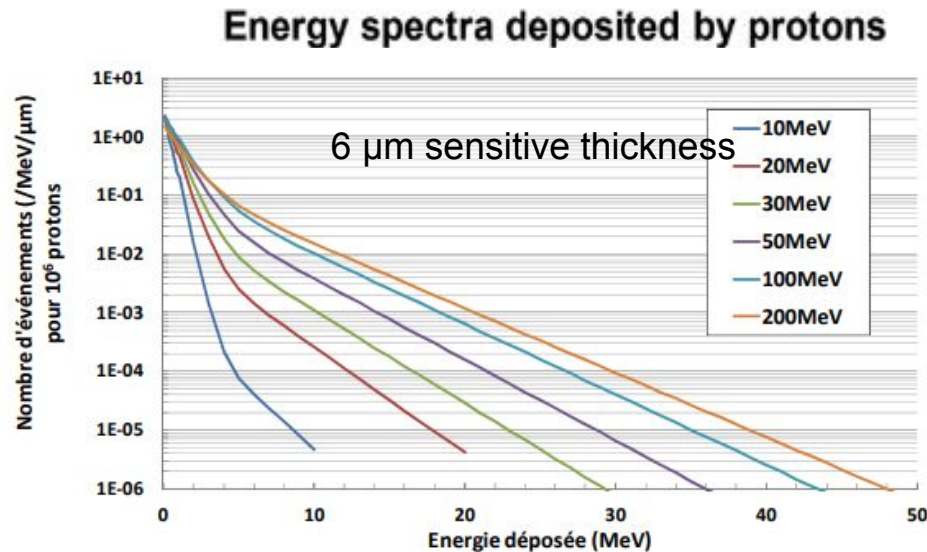
# SIMPA methodology



IRPP model:  
 $Ed = LET \times \text{sensitive thickness}$

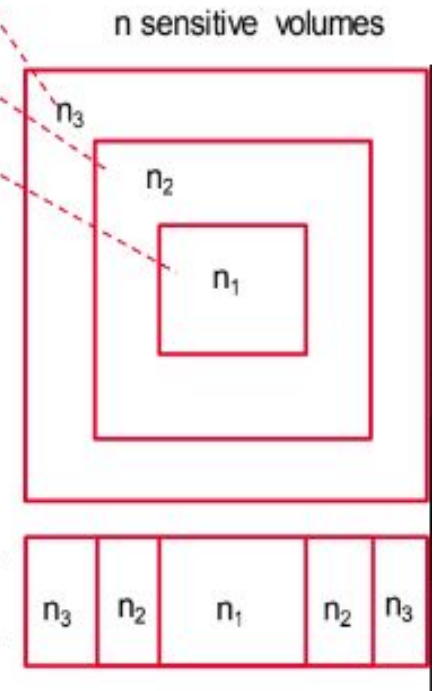


The heavy-ion cross-section ( $\sigma_{HI}$ ) is expressed as a function of deposited energy by multiplying the LET by the charge collection depth.



Proton cross section

Sensitive thickness

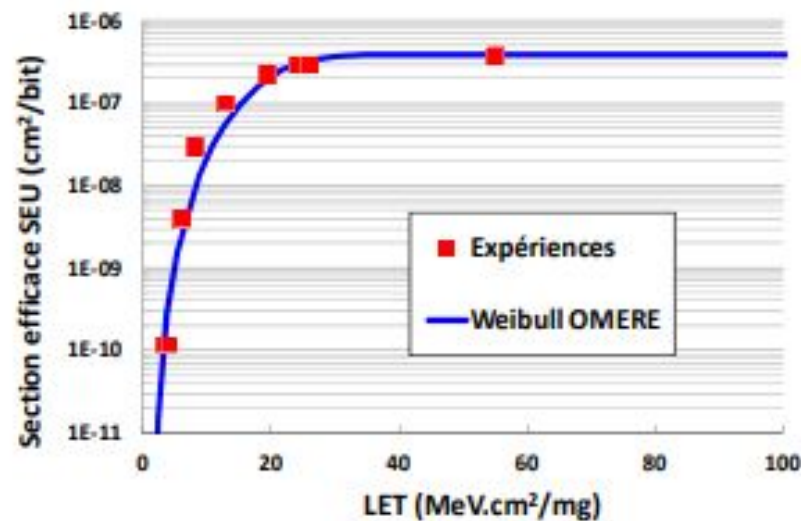


Valid for protons > 30 MeV

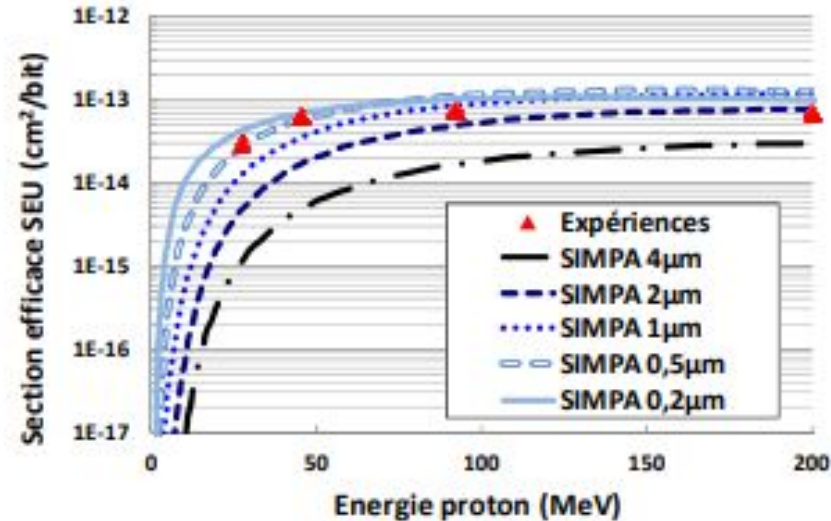
# SIMPA parameters

- The only parameter which remains difficult to evaluate is the sensitive thickness.
- An overestimation of the thickness does not mean an overestimation of the predicted proton cross-section.

Exemple: HM62832 SRAM



Heavy ion data



SIMPA predictions

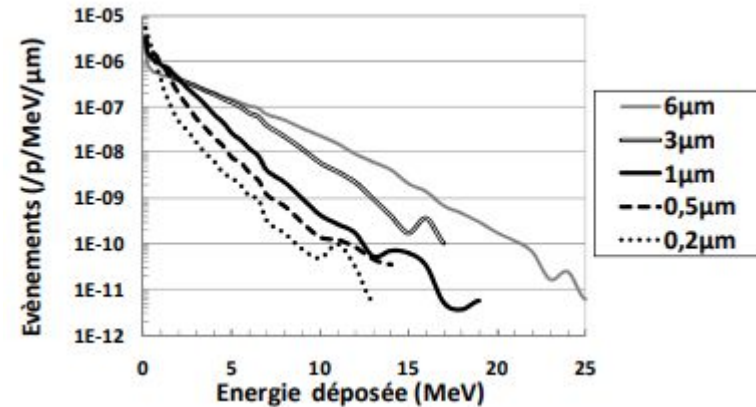


# SIMPA limitations

- 40% of SEU in 65nm SRAMs are induced by deposited energy < 3 MeV
- Not adapted for small sensitive volumes (nanoscale devices) due to 2 assumptions:

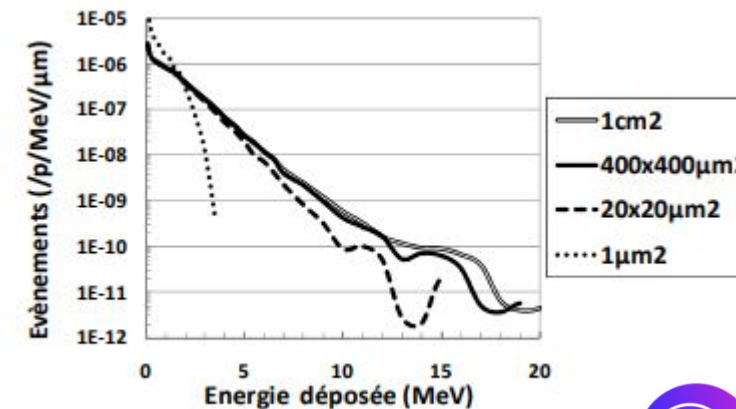
- The deposited energy/ $\mu\text{m}$  does not depend on sensitive thickness

- Experiments on diodes with  $\sim 6\mu\text{m}$  sensitive thickness
- Simulation data with thickness from 2 to 20  $\mu\text{m}$
- Sensitive thickness of 6  $\mu\text{m}$  in OMERE



200 MeV protons in  
400x400  $\mu\text{m}^2$   
vs sensitive thickness

- The deposited energy/ $\mu\text{m}$  does not depend on sensitive area



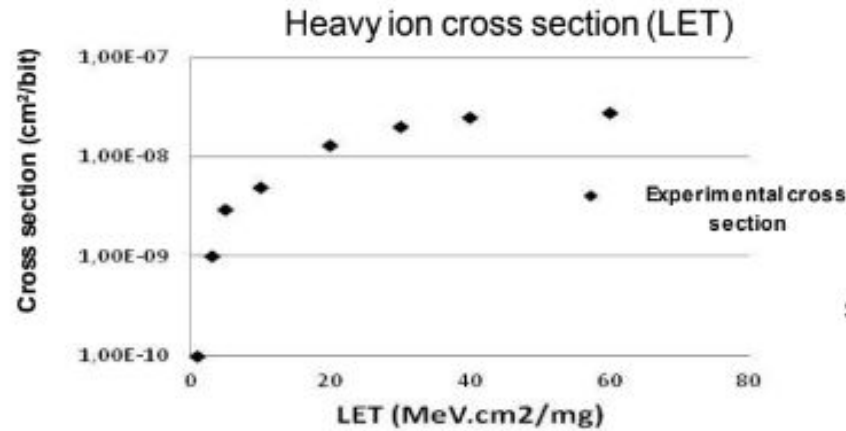
200 MeV protons for  
1  $\mu\text{m}$  sensitive  
thickness  
vs sensitive area

# METIS overview

- **Monte-Carlo Engineering Tool for Ion-induced SEE**
- Proposed by Airbus in 2011
- SEU prediction in bulk SRAMs
- Similar to SIMPA, critical energy and sensitive volumes are deduced from heavy ion data, sensitivity is completely characterized by a unity collection efficiency and composite RPP volumes with associated critical energies.
- But
  - Monte-Carlo selection of the nuclear reactions.
  - No free parameters: for each of the RPP sensitive volumes, the depth is half of the lateral length since the ambipolar diffusion mechanisms is predominant on deep-submicron technologies.
- Available in OMERE since 2018 (from version 5.2) (CNES funding): no more fully Monte-Carlo, same inputs will induce a single result.



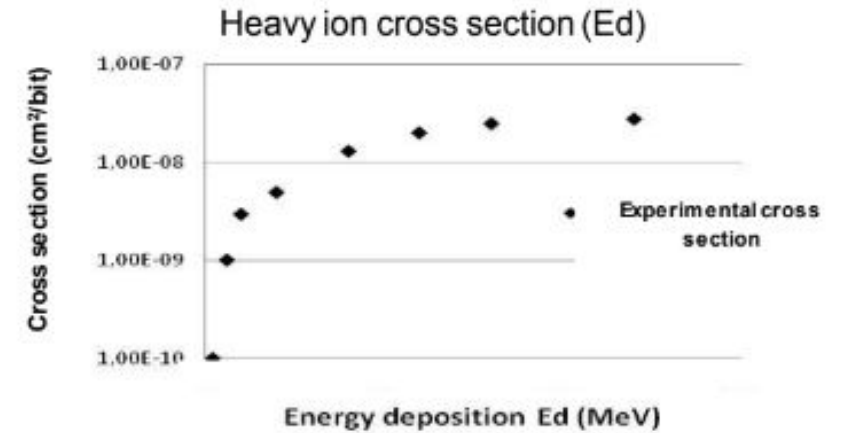
# METIS methodology



$$E_d = \text{LET} \times \text{sensitive thickness}$$



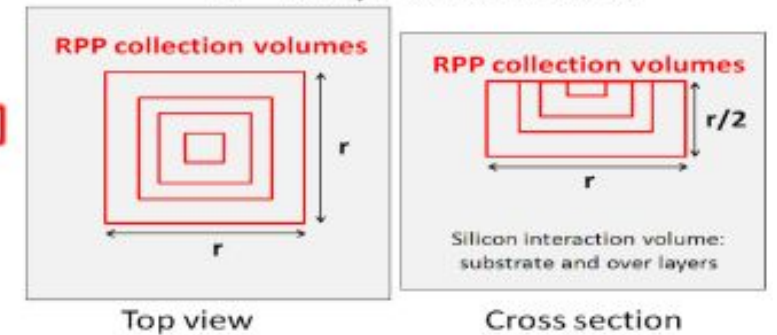
sensitive thickness = half of the surface side (variable)



Energy deposition  $E_d$  (MeV)

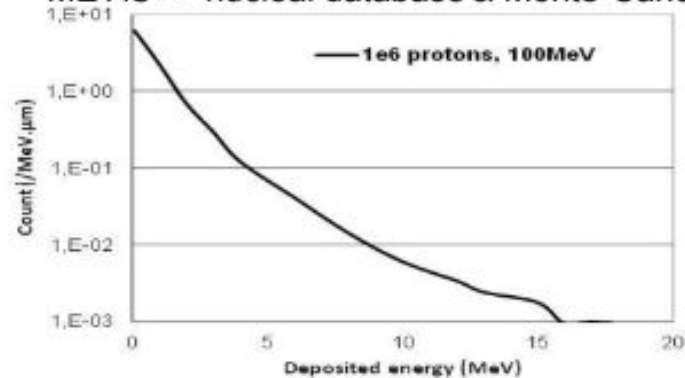
RPP model  
(multiple sensitive volumes)

$r^2 = \text{heavy ion cross section}$



Proton  
cross section

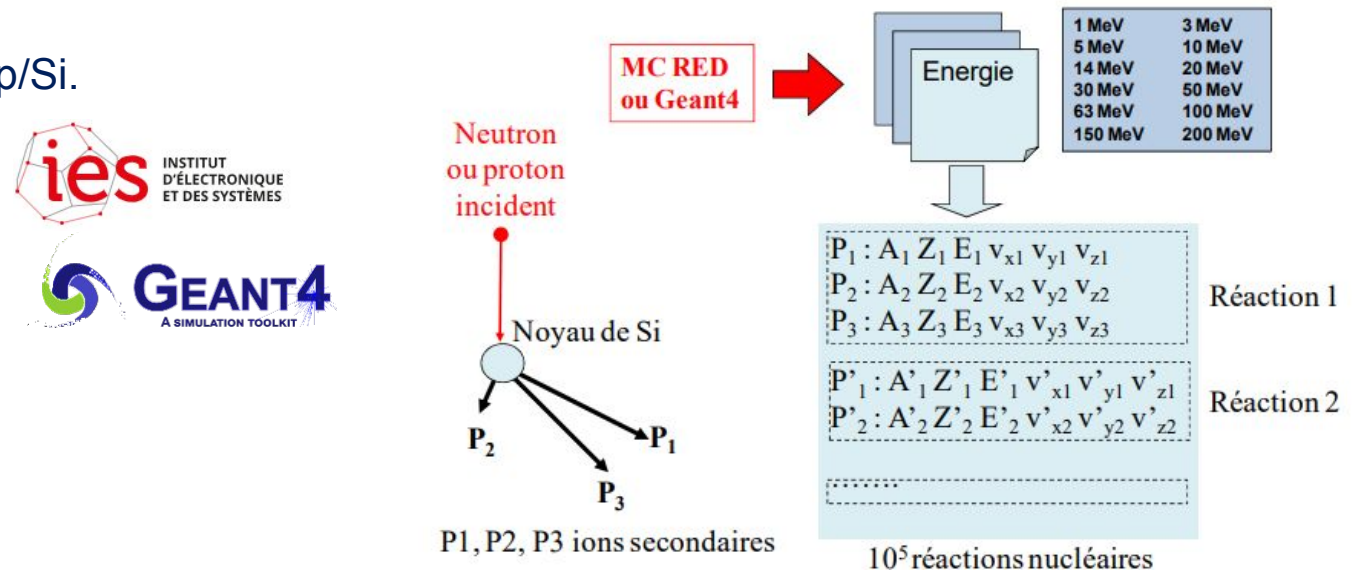
Energy spectra deposited by protons  
SIMPA => experimental data & analytical formula  
METIS => nuclear database & Monte-Carlo





# METIS nuclear database

- Monte-Carlo analysis of nuclear interactions induced by protons from precalculated nuclear databases
- Nuclear databases contain elastic scattering and non-elastic nuclear reactions
- Provide a detailed history of secondary ions from p/Si.
- MC-RED (IES) or GEANT4 nuclear physic codes
- Interaction volume  $20 \times 20 \times 80 \times \mu\text{m}^3$  : trade-off between computing time and accuracy
- Easy to adapt other materials than Si
- Silicon simplification:
  - Little impact of  $\text{SiO}_2$  on SEU prediction in bulk commercial technologies down to 90 nm (not valid for SOI technologies)
  - No impact of Tungsten on SEU prediction (low threshold LET)

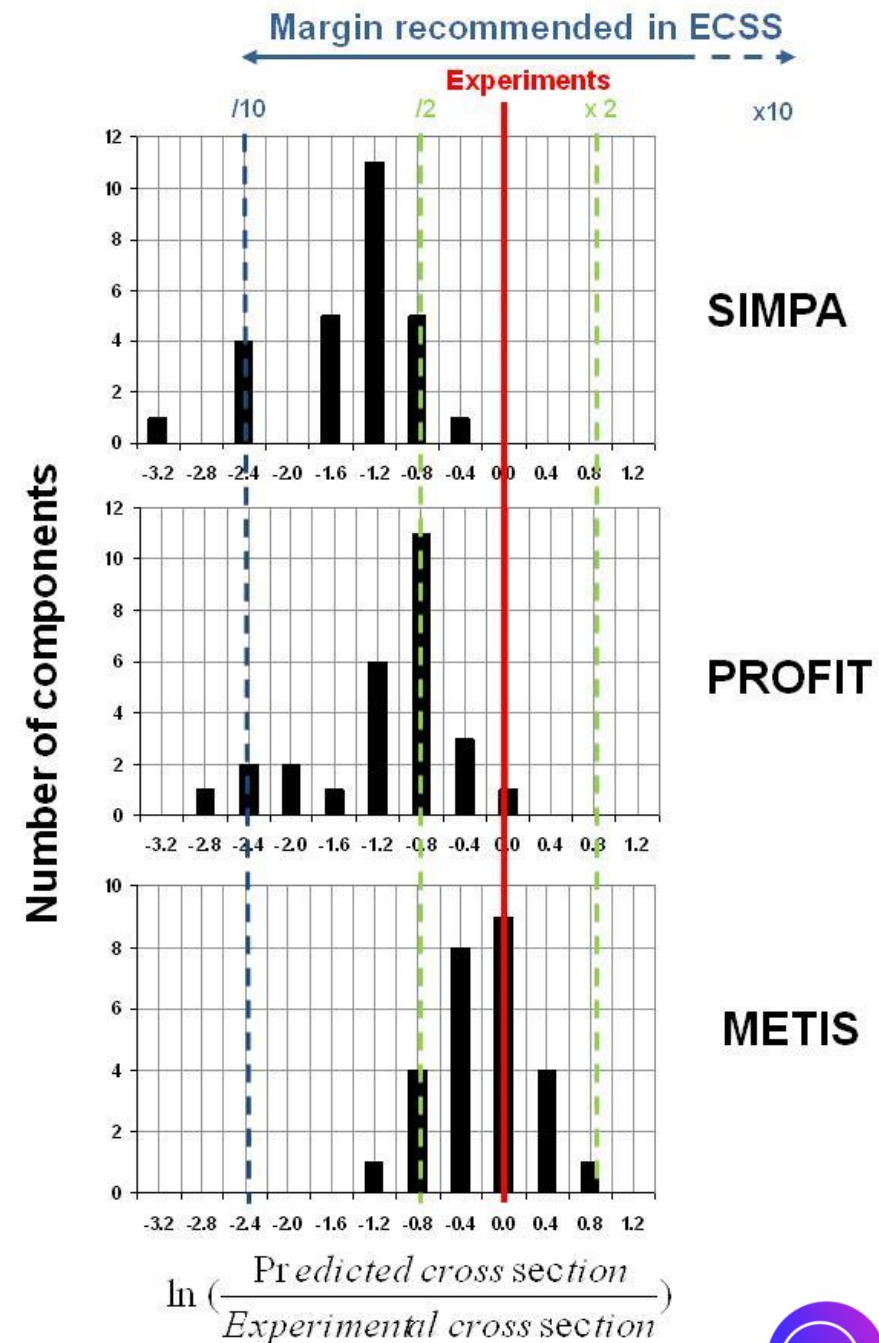


# METIS methodology

- Initial validation on ~30 devices from 500 nm down to 45 nm CMOS (bulk & SOI) technologies
- From 2012 to 2017, validation on a large number of state of the art devices, down to 16 nm.
- Within a factor of 3 for the XS and SER (comparison with the one given by a Weibull function of the proton data)
- For SOI SRAMs METIS is less accurate, an RPP geometry with varying thickness is not appropriate for SOI-based devices (the diffusion mechanism will be not predominant) and nuclear reactions with Oxygen have to be considered.
- For FinFET SRAMs:
  - Different shape of the sensitive volume, the diffusion mechanism will not be predominant
  - Cell variability in the SEU response

# METIS validation

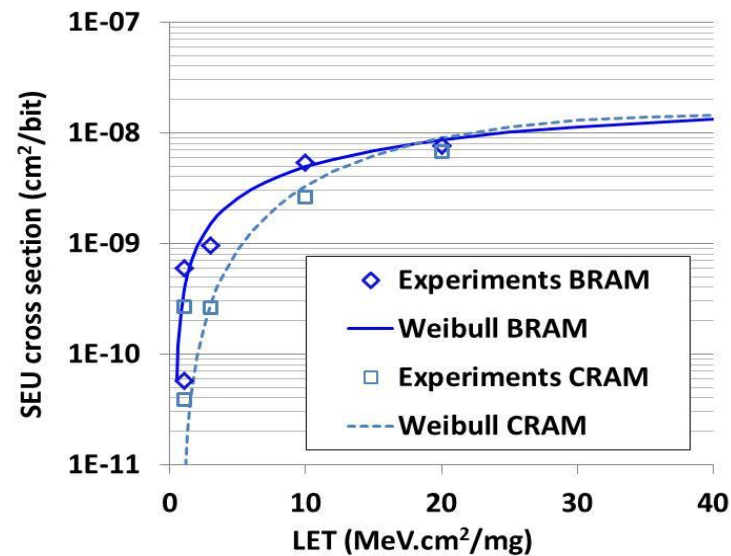
- Comparison with PROFIT & SIMPA
- ~ 30 devices : From 500 nm to 45 nm CMOS commercial (bulk & SOI) technologies
- 50 MeV proton XS
- Dispersion of the natural logarithm of the ratio of simulation to experiment
- METIS gives the most accurate predictions in 96% of tested cases




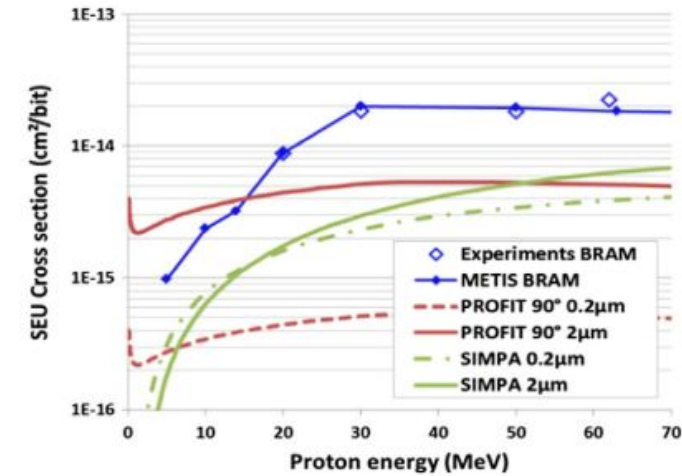
[ Airbus Amber ]

# METIS validation

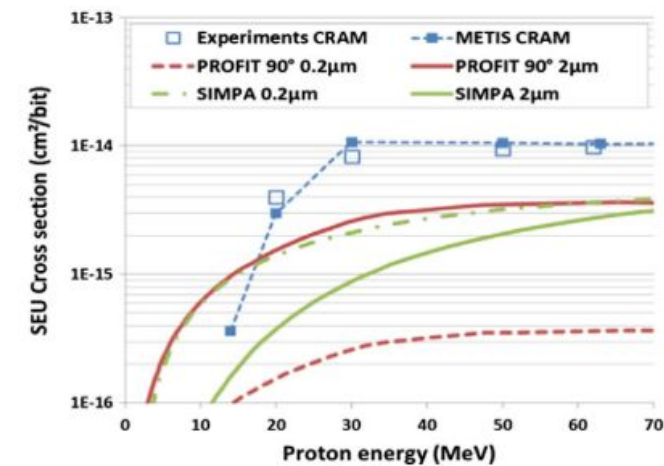
- 45 nm SRAM based FPGA (Spartan-6)



METIS  
  
 SIMPA  
 PROFIT



Block RAM  
 BRAM




Configuration  
 memory  
 CRAM

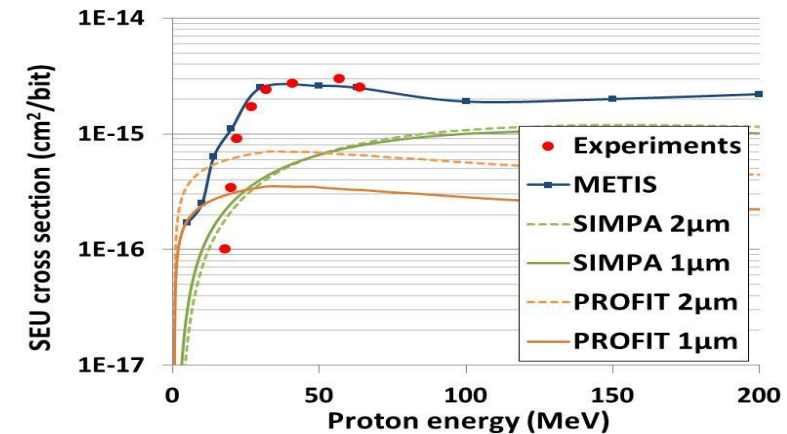
# METIS validation

- 20nm Xilinx UltraScale FPGA

Heavy ion data - Weibull

Saturation cross section (cm <sup>2</sup> /bit)	2x10 <sup>-9</sup>
Threshold LET (MeV-cm <sup>2</sup> /mg)	0.8
Width (MeV-cm <sup>2</sup> /mg)	12
S	1.5

METIS  
  
 SIMPA  
 PROFIT



Configuration  
memory  
CRAM

\*"Single-Event Characterization of the 20 nm Xilinx Kintex UltraScale Field-Programmable Gate Array under Heavy Ion Irradiation," 2015.

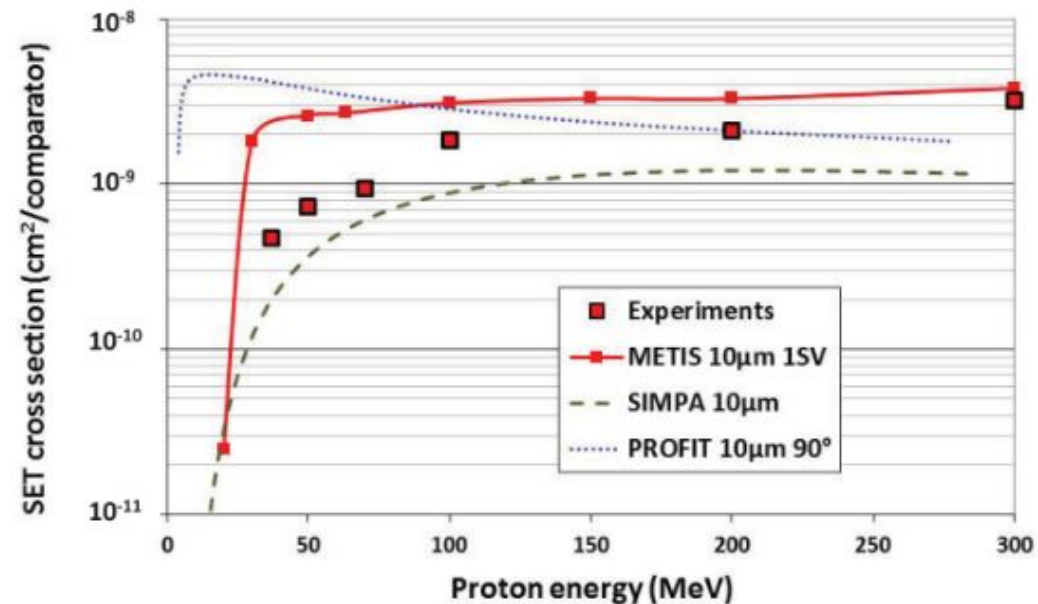
"Neutron, 64 MeV proton, thermal neutron and alpha single-event upset characterization of Xilinx 20nm UltraScale Kintex FPGA," 2015.



# Extended METIS

- METIS predictions using constant sensitive thickness (not possible in OMERE)  
in order to cover other SEEs such as SEL, SEU in DRAMS, analog SET in linear devices  
The diffusion mechanisms is no more predominant  
Large impact of the thickness

SET in LM139  
Proton experiments compared with  
METIS, SIMPA and PROFIT results  
using a sensitive thickness of 10  $\mu\text{m}$ .



- Multiple SEU (MCU) based on the definition of the cell size

# METIS limitations and current status

- For feature size < 32nm bulk or 65nm SOI, particularly in FinFETs, variability in direct ionization (LET fluctuations, spatial energy deposition) is becoming a dominant process
- No further development / activities since 2018 when METIS was implemented the OMERE tool
- RADECS 2021 & IEEE TNS 2022, D. L. Hansen, "Proton cross-sections from heavy-ion data: a review of the models": *The METIS model had the best performance of the MC models.*

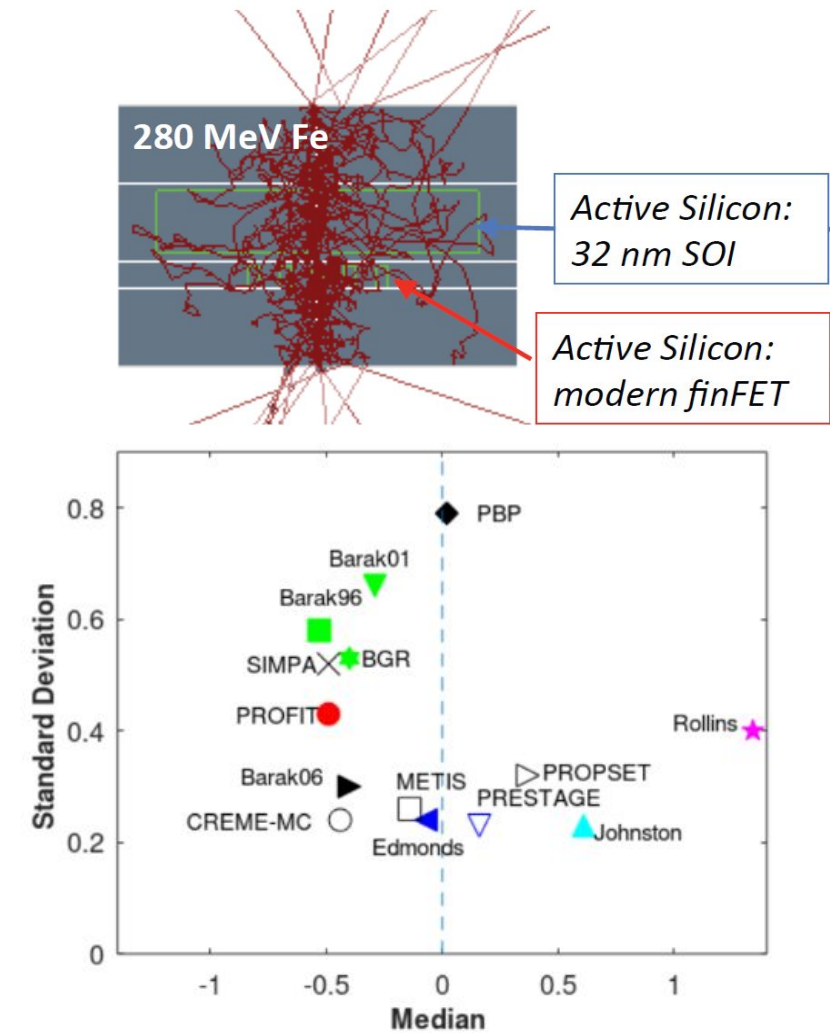


Fig. 4. Plot of median and standard deviation data from Table II. MC models are shown as hollow symbols. The origin represents perfect agreement.

# Summary

	<b>SIMPA</b>	<b>METIS in OMERE</b>	<b>METIS extended</b>
	Semi-empirical	Monte-Carlo	
<b>Year</b>	1989-1995	2011	2014
<b>Company</b>	MATRA MARCONI SPACE	Airbus	
<b>SEE</b>	SEU with sensitive thicknesses > 2 $\mu\text{m}$	SEU in deep submicron non-hardened SRAM like memories	SET, SEL, SEU in SDRAMs
<b>Inputs</b>	$\sigma_{\text{HI}}(\text{LET})$ + sensitive thickness	$\sigma_{\text{HI}}(\text{LET})$ (sensitive thickness = $0.5 \sigma_{\text{HI}}^{1/2}$ )	$\sigma_{\text{HI}}(\text{LET})$ + sensitive thickness
<b>Criteria</b>	Critical energy		
<b>Sensitive volumes</b>	IRPP		
<b>Nuclear data</b>	Experimental energy deposition (diodes)	MC selection of nuclear reactions	
<b>Time-efficiency</b>	<1s	1 min	

# Conclusion

- Underestimation of SIMPA predictions for SRAM < 1µm.
- METIS is a compromise between analytic approaches and Monte-Carlo based tools in order to get a fast and accurate engineering tool.
- Validated down to 20 nm bulk planar process (SEU in SRAMs).
- No validation below 20 nm and strong limitations
- Other models for proton cross section predictions based on heavy ion data
  - BGR (Burst Generation Rate)
  - PROFIT
  - Edmonds
  - Barak ...

# Publications

## SIMPA

- T. Bion and J. Bourrieau, “*A model for proton-induced SEU*,” IEEE Trans. Nucl. Sci., vol. 36, no. 6, pp. 2281–2286, Dec. 1989.
- B. Doucin, Y. Patin, J.P. Lochard, J. Beaucour, T. Carriere, D. Isabelle, J. Buisson, T. Corbiere, and T. Bion, “*Characterization of proton interactions in electronic components*,” IEEE Trans. Nucl. Sci., vol. 41, no. 3, pp. 593–600, Jul. 1994.
- B. Doucin, T. Carriere, C. Poivey, P. Garnier, J. Beaucour, and Y. Patin, “*Model of single event upsets induced by space protons in electronic devices*,” in Proc. 3rd Eur. Conf. Radiat. Effects Compon. Syst., 1995.

## METIS

- C. Weulersse, F. Wrobel, F. Miller, T. Carrière, R. Gaillard, J-R Vaillé, and N. Buard, “*A Monte-Carlo engineer tool for the prediction of SEU proton cross section from heavy ion data*,” in Proc. 12th Eur. Conf. Radiat. Effects Compon. Syst., Biarritz, France, Sep. 2011, pp. 376–383.
- C. Weulersse, F. Miller, T. Carrière, and R. Mangeret, “*Prediction of proton cross sections for SEU in SRAMs and SDRAMs using the METIS engineer tool*,” in Microelectronics Reliability. 55. 10.1016/j.microrel.2015.06.117.
- C. Weulersse, S. Morand, F. Miller, T. Carrière, and R. Mangeret, “*Simulation of proton induced SET in linear devices and assessment of sensitive thicknesses*,” 2015 15th European Conference on Radiation and Its Effects on Components and Systems (RADECS), Moscow, 2015, pp. 1-4. doi: 10.1109/RADECS.2015.7365668.
- C. Weulersse, S. Morand, F. Miller, T. Carrière, and R. Mangeret, “*Predictions of proton cross-section and sensitive thickness for analog Single-Event Transients*,” IEEE Transactions on Nuclear Science. 63. 10.1109/TNS.2016.2541692.

## Overview of models

- D. L. Hansen, D. Czajkowski, and B. Vermeire, “*Proton cross-sections from heavy-ion data: a review of the models*,” IEEE Trans. Nucl. Sci., vol. 69, 2022.